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A simple Design Example for a CS Amplifier

Given $\mu C_{ox} = 100 \mu A/V^2$, $L = 0.8 \mu$

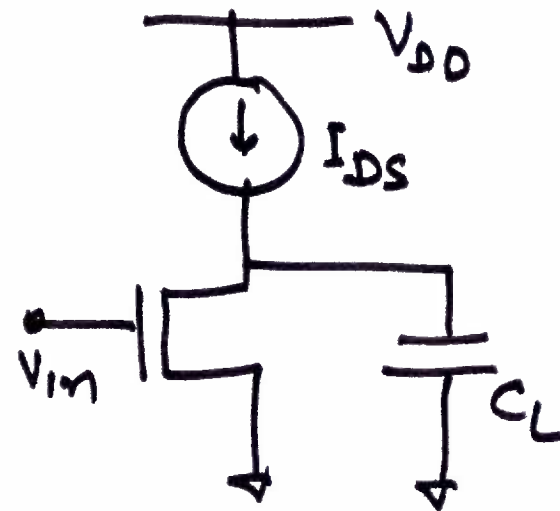
$$V_A = 50V$$

$$\alpha = 1.25$$

$$C_L = 0.1 \text{ pf}$$

$$BW = 2 \text{ MHz}$$

$$\text{Gain} \geq 200$$

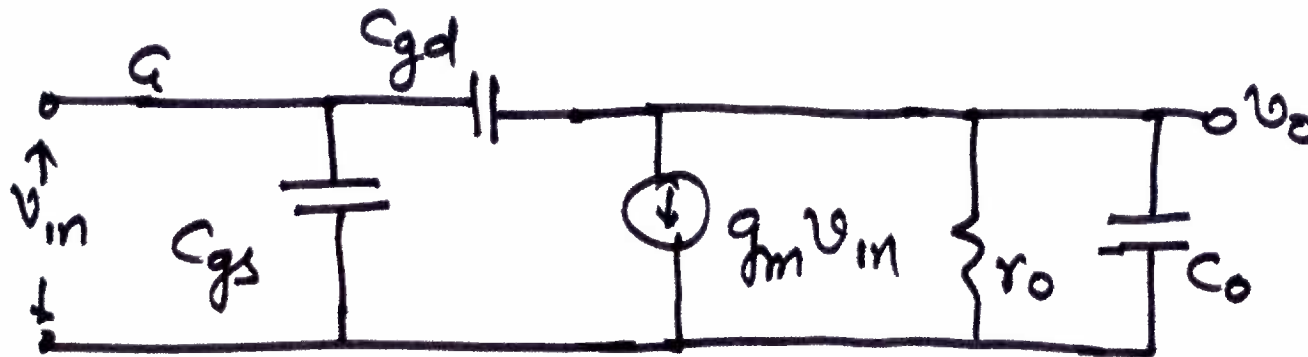


Equivalent Circuit (First Order)



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Using Kirchoff law

Assume
 $\frac{1}{\omega C_{gs}} \rightarrow \infty$

$$s C_{gd} (v_{in} - v_o) - g_m v_{in} - \frac{v_o}{r_o} - s C_o v_o = 0$$

$$v_{in} (s C_{gd} - g_m) - v_o (s C_{gd} + \frac{1}{r_o} + s C_o) = 0$$

$$\text{or } \frac{v_o}{v_{in}} = - \frac{g_m - s C_{gd}}{\frac{1}{r_o} + s (C_{gd} + C_o)}$$

$$r \text{ } A_v(s) = \frac{V_o(s)}{V_m(s)} = -g_m r_o \frac{1 - s C_{gd} / g_m}{1 + s r_o (C_{gd} + C_o)}$$

$$A_v(s) = + A_v(0) \frac{1 - s C_{gd} / g_m}{1 + s (r_o \cdot C_L)}$$

$$C_o \approx C_{gd} = C_L$$

We have 1 'zero' and 1 'pole'.

Neglect 'zero' assuming it is far off compared to pole frequency

This is possible in most cases as $r_o \gg \frac{1}{g_m}$



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$$\text{Then } A_V(s) = A_{V0} \frac{1}{1 + s \cdot r_o C_L}$$

$$\therefore \text{Bandwidth} = \frac{1}{r_o C_L} = \omega_{-3db}$$

$$\text{and D.C. Gain} = A_{V0} = -g_m r_o$$

Then Gain Bandwidth Product GBW is

$$= \frac{g_m}{C_L}$$

Using these expressions we solve over
Problem



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$$g_m = \sqrt{2 \frac{\beta}{\alpha} I_{DS}}$$

Fixed I_{DS} biasing

$$r_o \cong \frac{V_A}{I_{DS}}$$



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(i) We start with r_o

$$r_o = \frac{1}{2\pi \cdot BW \cdot C_L} = \frac{1}{6.28 \times 2 \times 10^6 \times 10^{-13}}$$
$$\cong 0.8 \text{ M}\Omega$$

cii) I_{DS} evaluation

$$I_{DS} = \frac{V_A}{r_o} = \frac{50}{0.8 \times 10^6} \cong 62.5 \text{ }\mu\text{A} = 62.5 \text{ }\mu\text{A}$$



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$$\text{Now } |A_{vo}| = g_m r_o$$

$$\therefore g_m = \frac{240}{0.8 \times 10^6} = 300 \times 10^{-6} \text{ S}$$

$$\text{But } g_m = \sqrt{\frac{2 \mu_{\text{cox}} (W/L) I_{DS}}{\alpha}}$$

$$\therefore \frac{W}{L} = \frac{g_m^2 \alpha}{2 \mu_{\text{cox}} I_{DS}} = \frac{(300 \times 10^{-6})^2 \times 1.25}{2 \times 100 \times 10^{-6} \times 62.5 \times 10^{-6}}$$

≈ 9

Given $L = 0.8 \mu$ \therefore $W = 0.72 \mu$

We see

$$\frac{g_m}{I_{D1}} = \frac{300 \times 10^{-6}}{62.5 \times 10^{-6}} = \frac{600}{125} = \frac{24}{5}$$

= 4.8 (Per Volt)



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Modification

Lets put limit on I_{D1} to lower value (Lower Power) Dissipation

We have seen that $W \propto \frac{1}{V_{ov}} \sim \frac{g_m}{I_{D1}}$

\therefore If I use lower I_{D1} , I need Larger Width Device.

If SPECS say 'Reduced Area' is necessary

This can be actually done by optimisation.

However Long Channel Model may not suffice

If Design requires smaller area for the circuit, ~~then~~ as well as Low Power, we have trade-off at hand.

For lower Power, we reduce I_{DS}

Hence for a fixed g_m (Gain constant), $\frac{g_m}{I_{DS}}$ increases. Since $\frac{1}{V_{OV}} \propto \frac{g_m}{I_{DS}}$, reduction in V_{OV} will occur at lower I_{DS} .

But $W \propto \frac{1}{V_{OV}}$, which means W will increase at reduced I_{DS} . Which in turns means Increase of area

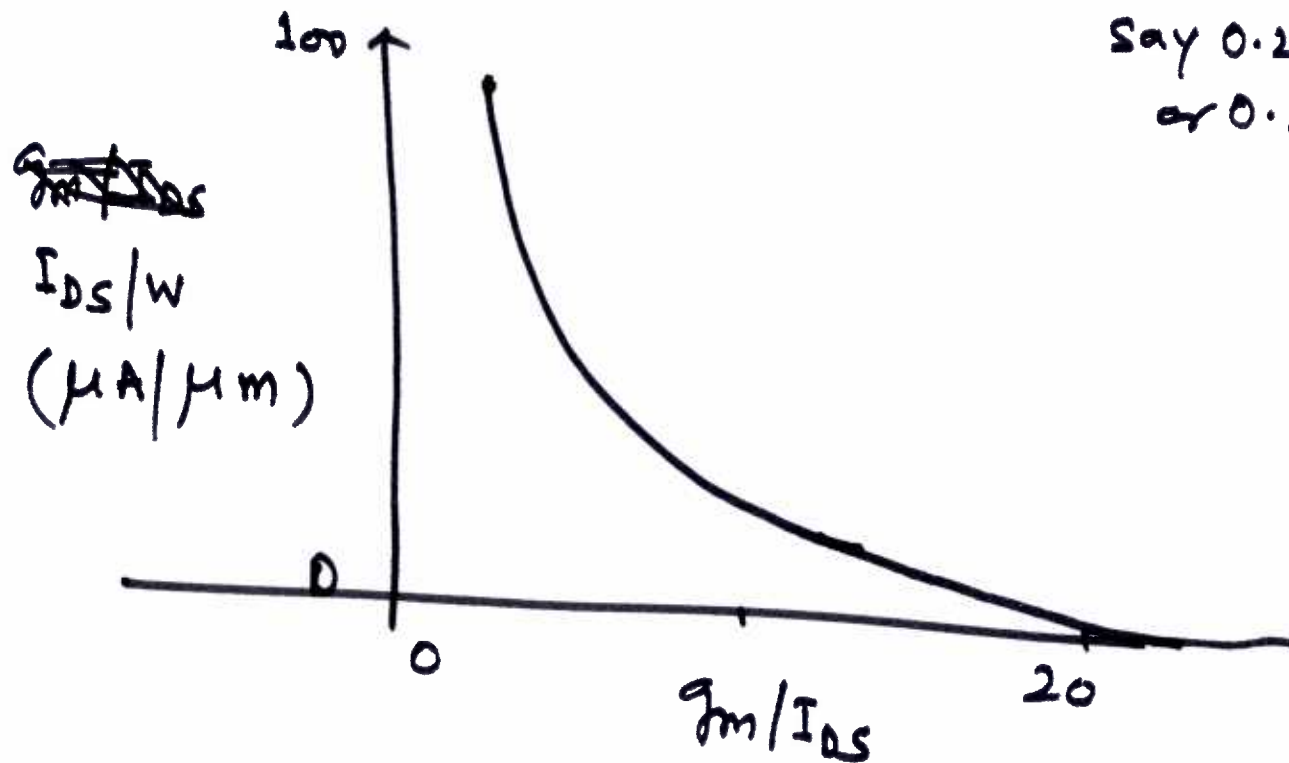


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We use $\frac{g_m}{I_{DS}}$ as Design Variable, then
we plot I_{DS}/W as g_m/I_{DS} (For a Tech)
node

Say 0.25μ .
or 0.35μ



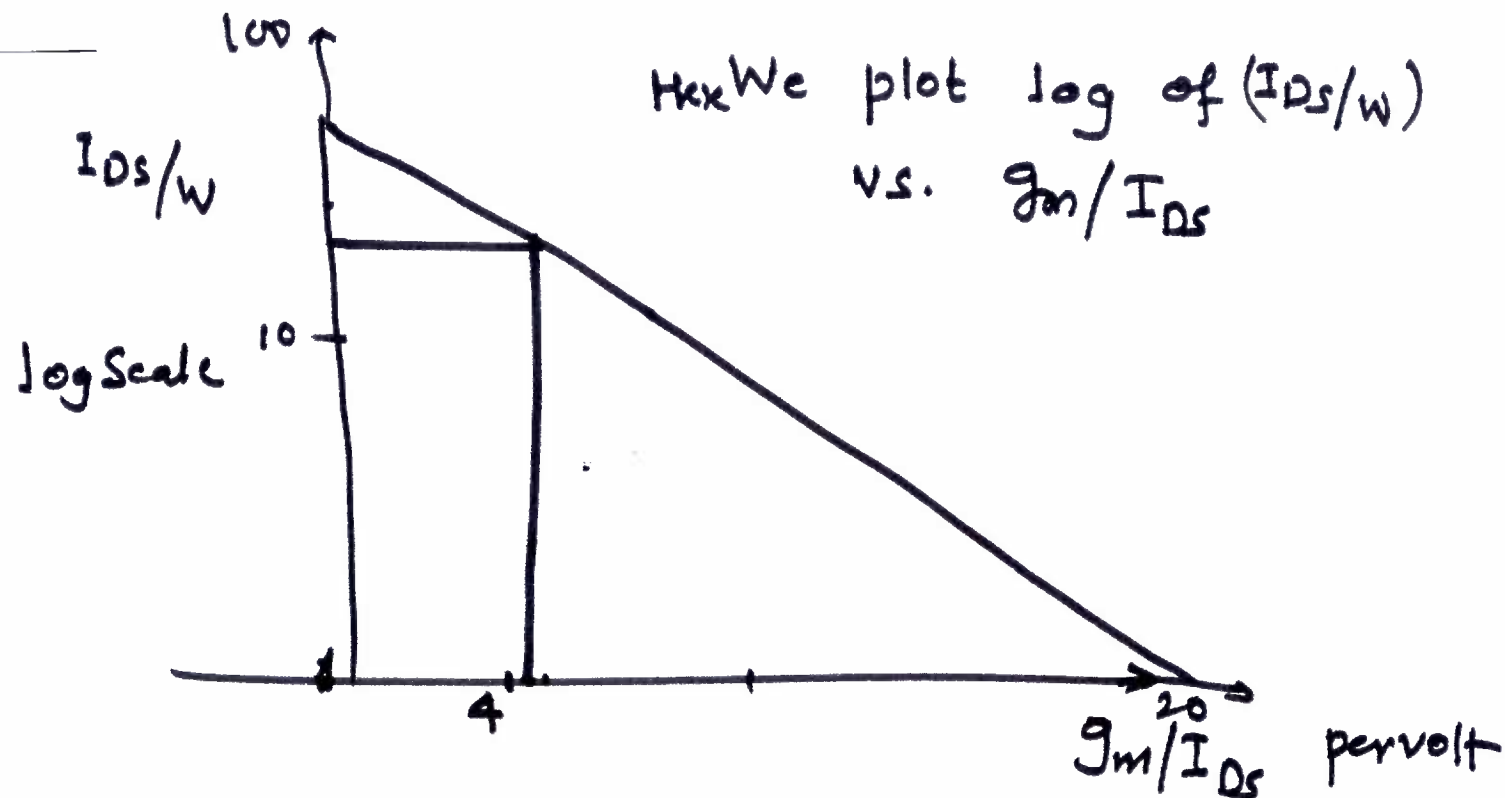
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For our problem $g_m/I_{DS} = 4.8 \text{ V}^{-1}$

Let us say from graph
we have $\frac{I_{DS}}{W} \approx 40 \mu\text{A}/\mu\text{m}$ for $g_m/I_{DS} = 4.8 \text{ V}^{-1}$

But we have $I_{DS} = 62.5 \mu\text{A}$ $\therefore W = \frac{I_{DS}}{I_{DS}/W} = \frac{62.5}{40}$

$\therefore W = \frac{12.5}{8} = 1.56 \mu\text{m}$